SEMICONDUCTOR

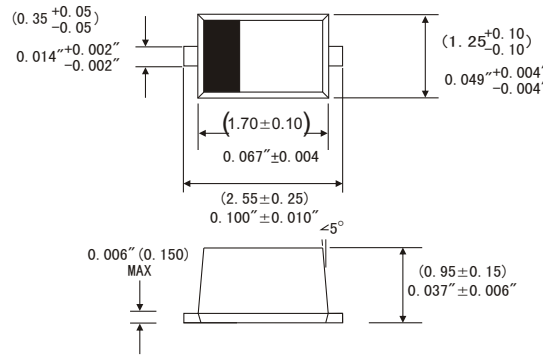
MM3Z2V0 THRU MM3Z120

0.3W SILICON PLANAR ZENER DIODES

FEATURES

- Total power dissipation: max. 300 mW
- Small plastic package suitable for surface mounted design
- Tolerance approximately ±5%
- High temperature soldering guaranteed: 260℃/10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

SOD-323



Dimensions in inches and (millimeters)

MECHANICAL DATA

- *Case*: SOD-323 plastic case
- *Weight*: Approx. 0.004 gram

ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES) (T_A=25℃)

	Symbols	*Value*	*Units*
Zener current see table "Characteristics"			
Power dissipation	P_{tot}	300	mW
Junction temperature	T_J	150	℃
Storage temperature range	T_{STG}	-55 to+150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃)

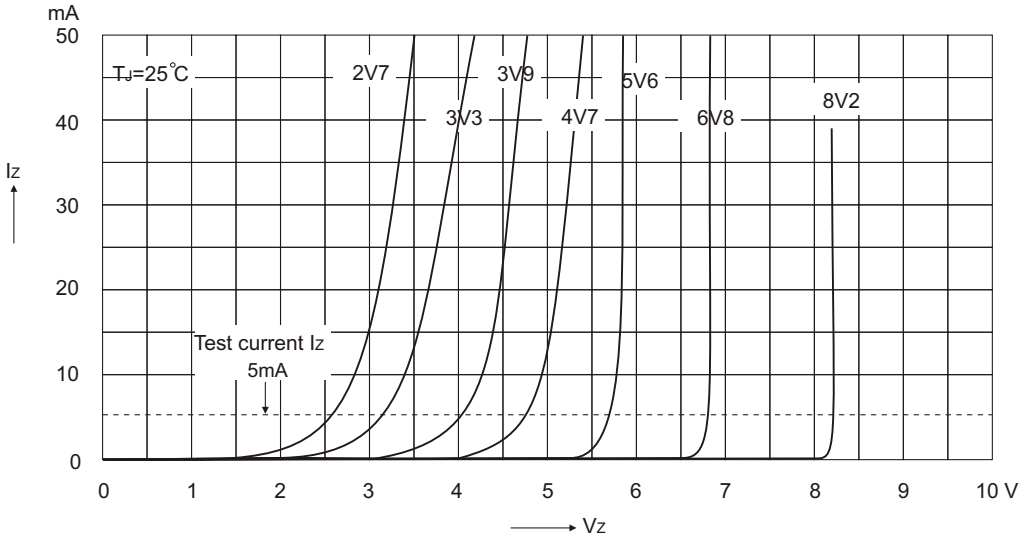
	Symbols	*Min*	*Typ*	*Max*	*Units*
Thermal resistance junction to ambient	$R_{\theta JA}$			300	K/W
Forward voltage at I_F=10mA	V_F			0.9	V

MM3Z... SILICON PLANAR ZENER DIODES

Type	Marking Code	Zener Voltage range 1)			Dynamic resistance 2)		Reverse leakage current		Temp Coefficient of zener voltage
		V_{ZNOM}	I_{ZT} for V_{ZT}		r_{zj} and r_{zjK} at I_{ZK}		I_R and I_R at V_R		TK_{VZ}
		V	mA	V	Ω	mA	μA	V	%/K
MM3Z2V0	B0	2.0	5	1.80…2.15	100	5	120	0.5	-0.09…-0.06
MM3Z2V2	C0	2.2	5	2.08…2.33	100	5	120	0.7	-0.09…-0.06
MM3Z2V4	1C	2.4	5	2.28…2.56	100	5	120	1	-0.09…-0.06
MM3Z2V7	1D	2.7	5	2.5…2.9	110	5	120	1	-0.09…-0.06
MM3Z3V0	1E	3.0	5	2.8…3.2	120	5	50	1	-0.08…-0.05
MM3Z3V3	1F	3.3	5	3.1…3.5	130	5	20	1	-0.08…-0.05
MM3Z3V6	1H	3.6	5	3.4…3.8	130	5	10	1	-0.08…-0.05
MM3Z3V9	1J	3.9	5	3.7…4.1	130	5	5	1	-0.08…-0.05
MM3Z4V3	1K	4.3	5	4…4.6	130	5	5	1	-0.06…-0.03
MM3Z4V7	1M	4.7	5	4.4…5	130	5	2	1	-0.05…+0.02
MM3Z5V1	1N	5.1	5	4.8…5.4	130	5	2	1.5	-0.02…+0.02
MM3Z5V6	1P	5.6	5	5.2…6	80	5	1	2.5	-0.05…+0.05
MM3Z6V2	1R	6.2	5	5.8…6.6	50	5	1	3	0.03…0.06
MM3Z6V8	1X	6.8	5	6.4…7.2	30	5	0.5	3.5	0.03…0.07
MM3Z7V5	1Y	7.5	5	7…7.9	30	5	0.5	4	0.03…0.07
MM3Z8V2	1Z	8.2	5	7.7…8.7	30	5	0.5	5	0.03…0.08
MM3Z9V1	2A	9.1	5	8.5…9.6	30	5	0.5	6	0.03…0.09
MM3Z10	2B	10	5	9.4…10.6	30	5	0.1	7	0.03…0.1
MM3Z11	2C	11	5	10.4…11.6	30	5	0.1	8	0.03…0.11
MM3Z12	2D	12	5	11.4…12.7	35	5	0.1	9	0.03…0.11
MM3Z13	2E	13	5	12.4…14.1	35	5	0.1	10	0.03…0.11
MM3Z15	2F	15	5	13.8…15.6	40	5	0.1	11	0.03…0.11
MM3Z16	2H	16	5	15.3…17.1	40	5	0.1	12	0.03…0.11
MM3Z18	2J	18	5	16.8…19.1	45	5	0.1	13	0.03…0.11
MM3Z20	2K	20	5	18.8…21.2	50	5	0.1	15	0.03…0.11
MM3Z22	2M	22	5	20.8…23.3	55	5	0.1	17	0.04…0.12
MM3Z24	2N	24	5	22.8…25.6	60	5	0.1	19	0.04…0.12
MM3Z27	2P	27	5	25.1…28.9	70	2	0.1	21	0.04…0.12
MM3Z30	2R	30	5	28…32	80	2	0.1	23	0.04…0.12
MM3Z33	2X	33	5	31…35	80	2	0.1	25	0.04…0.12
MM3Z36	2Y	36	5	34…38	90	2	0.1	27	0.04…0.12
MM3Z39	2Z	39	2.5	37…41	100	2	2	30	0.04…0.12
MM3Z43	3A	43	2.5	40…46	130	2	2	33	0.04…0.12
MM3Z47	3B	47	2.5	44…50	150	2	2	36	0.04…0.12
MM3Z51	3C	51	2.5	48…54	180	2	1	39	0.04…0.12
MM3Z56	3D	56	2.5	52…60	180	2	1	43	0.04…0.12
MM3Z62	3E	62	2.5	58…66	200	2	0.2	47	0.04…0.12
MM3Z68	3F	68	2.5	64…72	250	2	0.2	52	0.04…0.12
MM3Z75	3H	75	2.5	70…79	300	2	0.2	57	0.04…0.12
MM3Z82	3J	82	2.5	77…87	300	2	0.2	63	0.05…0.12
MM3Z91	3K	91	1	85…96	700	1	0.2	69	0.05…0.12
MM3Z100	3M	100	1	94…106	700	1	0.2	76	0.05…0.12
MM3Z110	3N	110	1	104…116	800	1	0.2	84	0.05…0.12
MM3Z120	3P	120	1	114…127	900	1	0.2	91	0.05…0.12

1) V_Z is teated with pulses tp=20ms.
2) Z_Z is measured at I_Z by given a very small A. C. current signal.

BREAKDOWN CHARACTERISTICS AT T_J= CONSTANT (PULSED)



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